

**CMHD4150**  
**SURFACE MOUNT**  
**HIGH SPEED SWITCHING DIODE**



**SOD-123 CASE**

# Central<sup>TM</sup>

**Semiconductor Corp.**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMHD4150 type is a high speed silicon switching diode manufactured by the epitaxial planar process, in an epoxy molded surface mount package, designed for high speed switching applications.

**Marking code is C50**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

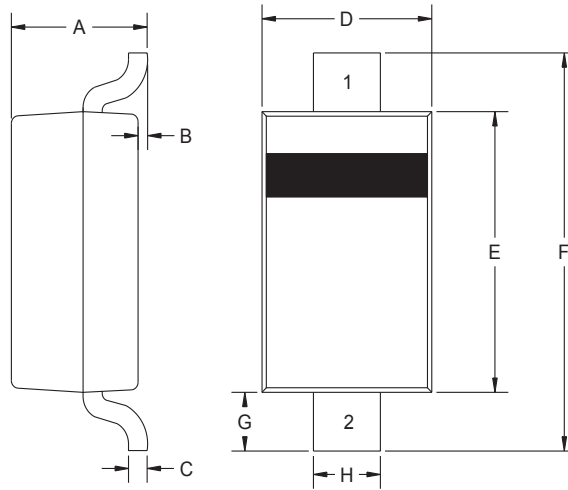
	<u>SYMBOL</u>		<u>UNITS</u>
Continuous Reverse Voltage	$V_R$	50	V
Peak Repetitive Reverse Voltage	$V_{RRM}$	50	V
Continuous Forward Current	$I_F$	250	mA
Peak Repetitive Forward Current	$I_{FRM}$	250	mA
Forward Surge Current, $t_p=1$ msec.	$I_{FSM}$	4000	mA
Forward Surge Current, $t_p=1$ sec.	$I_{FSM}$	1000	mA
Power Dissipation	$P_D$	400	mW
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\Theta_{JA}$	312.5	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>MAX</u>	<u>UNITS</u>
$I_R$	$V_R=50\text{V}$		100	nA
$V_F$	$I_F=1.0\text{mA}$	0.54	0.62	V
$V_F$	$I_F=10\text{mA}$	0.66	0.74	V
$V_F$	$I_F=50\text{mA}$	0.76	0.86	V
$V_F$	$I_F=100\text{mA}$	0.82	0.92	V
$V_F$	$I_F=200\text{mA}$	0.87	1.0	V
$C_T$	$V_R=0, f=1$ MHz		4.0	pF
$t_{rr}$	$I_R=I_F=10\text{mA}, R_L=100\Omega, \text{Rec. to } 1.0\text{mA}$		4.0	ns

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**SOD-123 CASE - MECHANICAL OUTLINE**



R3

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.037	0.053	0.95	1.35
B	-	0.005	-	0.12
C	-	0.008	-	0.20
D	0.055	0.071	1.40	1.80
E	0.098	0.112	2.50	2.84
F	0.140	0.154	3.55	3.90
G	0.010	-	0.25	-
H	0.020	0.028	0.50	0.70

SOD-123 (REV:R3)

LEAD CODE:

- 1) Cathode
- 2) Anode

**MARKING CODE: C50**

R0 ( 24-August 2001)